These are stress ratings only and functional operation of the device at these ratings or any other above those indicated in the operation sections of the specifications below is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability and cause permanent damage to the device.

V	-0.3V to +6.0V
V _{cc} V+ (NOTE 1)	0.3V to +7.0V
V- (NOTE 1)	+0.3V to -7.0V
V+ + V- (NOTE 1)	+13V
I _{cc} (DC V _{cc} or GND current)	<u>+</u> 100mA

Input Voltages

TxIN,	-0.3V to +6.0V
RxIN	<u>+</u> 25V
Output Voltages	
	<u>+</u> 13.2V
RxOUT,	0.3V to (V _{cc} +0.3V)
Short-Circuit Duration	
TxOUT	Continuous
Storage Temperature	65°C to +150°C

<u>+</u>5.0

+5.4

Power Dissipation per package

16-pin SSOP (derate 9.69mW/°C above +70°C)......775mW 16-pin PDIP (derate 14.3mW/°C above +70°C)......1150mW 16-pin Wide SOIC (derate 11.2mW/°C above +70°C)......900mW 16-pin TSSOP (derate 10.5mW/°C above +70°C)......850mW

NOTE 1: V+ and V- can have maximum magnitudes of 7V, but their absolute difference cannot exceed 13V.

Jnless otherwise noted, the following specifications apply for V_{cc} = +3.0V to +5.5V with T_{AMB} = T_{MIN} to T_{MAX}					
PARAMETER	MIN.	TYP.	MAX.	UNITS	CONDITIONS
DC CHARACTERISTICS					
Supply Current		0.3	1.0	mA	no load, V_{cc} = 3.3V, T_{AMB} = 25°C, TxIN = GND or V_{cc}
LOGIC INPUTS AND RECEIV	/ER OUTP	UTS			
Input Logic Threshold LOW	GND		0.8	V	TxIN
Input Logic Threshold HIGH	2.0		Vcc	V	Vcc = 3.3V
Input Logic Threshold HIGH	2.4		Vcc	V	Vcc = 5.0V
Input Leakage Current		<u>+</u> 0.01	<u>+</u> 1.0	μA	TxIN, T _{AMB} = +25°C
Output Voltage LOW			0.4	V	I _{out} = 1.6mA
Output Voltage HIGH	V _{cc} -0.6	V _{cc} -0.1		V	I _{оит} = -1.0mА

V

ELECTRICAL CHARACTERISTICS

All driver outputs loaded with $3K\Omega$ to

GND, $T_{AMB} = +25^{\circ}C$

DRIVER OUTPUTS Output Voltage Swing

PARAMETER	MIN.	TYP.	MAX.	UNITS	CONDITIONS
DRIVER OUTPUTS (continued)					
Output Resistance	300			Ω	$V_{cc} = V + = V - = 0V, V_{out} = \pm 2V$
Output Short-Circuit Current	1	<u>+</u> 35	<u>+</u> 60	mA	V _{OUT} = 0V
Output Leakage Current			<u>+</u> 25	μA	$V_{cc} = 0V, V_{out} = \pm 12V$
RECEIVER INPUTS				Î	^
Input Voltage Range	-15		15	V	
Input Threshold LOW	0.6	1.2		V	Vcc = 3.3V
Input Threshold LOW	0.8	1.5		V	Vcc = 5.0V
Input Threshold HIGH		1.5	2.4	V	Vcc = 3.3V
Input Threshold HIGH		1.8	2.4	V	Vcc = 5.0V
Input Hysteresis		0.3		V	
Input Resistance	3	5	7	kΩ	
TIMING CHARACTERISTICS					<u>`</u>
Maximum Data Rate	460			Kbps	$R_L = 3K\Omega$, $C_L = 1000pF$, one driver switching
Driver Propagation Delay, t _{PHL}	1	1.0		μs	R _L = 3KΩ, C _L = 1000pF
Driver Propagation Delay, $t_{_{PLH}}$	1	1.0		μs	R _L = 3KΩ, C _L = 1000pF
Receiver Propagation Delay, $t_{_{PHL}}$		0.3		μs	Receiver input to Receiver output, C _L = 150pF
Receiver Propagation Delay, $t_{_{\text{PLH}}}$		0.3		μs	Receiver input to Receiver output, C _L = 150pF
Receiver Output Enable Time	1	200		ns	
Receiver Output Disable Time		200		ns	
Driver Skew	1	100	500	ns	t _{PHL} - t _{PLH}
Receiver Skew	1	200	1000	ns	t _{PHL} - t _{PLH}
Transition-Region Slew Rate		60		V/µs	Vcc = 3.3V, $R_L = 3k\Omega$, $T_{AMB} = 25^{\circ}$ C, measurements taken from -3.0V to +3.0V or +3.0V to -3.0V

TYPICAL PERFORMANCE CHARACTERISTICS

Unless otherwise noted, the following performance characteristics apply for V_{CC} = +3.3V, 460kbps data rate, all drivers loaded with 3k Ω , 0.1µF charge pump capacitors, and T_{AMB} = +25°C.



Figure 1. Transmitter Output Voltage vs Load Capacitance



Figure 3. Supply Current VS. Load Capacitance when Transmitting Data



Figure 2. Slew Rate vs Load Capacitance

PIN FUNCTION

SP3232EH_100_010611

NAME	FUNCTION	PIN NUMBER
	FUNCTION	SP3232EH
C1+	Positive terminal of the voltage doubler charge-pump capacitor	1
V+	+5.5V output generated by the charge pump	2
C1-	Negative terminal of the voltage doubler charge-pump capacitor	3
C2+	Positive terminal of the inverting charge-pump capacitor	4
C2-	Negative terminal of the inverting charge-pump capacitor	5
V-	-5.5V output generated by the charge pump	6
T₁OUT	RS-232 driver output.	14
T ₂ OUT	RS-232 driver output.	7
R₁IN	RS-232 receiver input	13
R ₂ IN	RS-232 receiver input	8
R₁OUT	TTL/CMOS receiver output	12
R₂OUT	TTL/CMOS receiver output	9
T₁IN	TTL/CMOS driver input	11
T ₂ IN	TTL/CMOS driver input	10
GND	Ground.	15
V _{cc}	+3.0V to +5.5V supply voltage	16

Table 1. Device Pin Description



Figure 4. Pinout Configuration for the SP3232EH

SP3232EH_100_010611



Figure 5. SP3232EH Typical Operating Circuit

The SP3232EH is a 2-driver / 2-receiver devices ideal for portable or hand-held applications. The SP3232EH transceiver meets the EIA/TIA-232 and ITU-TV.28/V.24 communication protocols and can be implemented in battery-powered, portable, or hand-held applications such as notebook or palmtop computers. The SP3232EH device features Exar's proprietary on-board charge pump circuitry that generates ±5.5V for RS-232 voltage levels from a single +3.0V to +5.5V power supply. This device is ideal for +3.3V-only systems, mixed +3.3V to +5.5V systems, or +5.0V-only systems that require true RS-232 performance. The SP3232EH device can operate at a minimum data rate of 460kbps when fully loaded.

THEORY OF OPERATION

The **SP3232EH** is made up of three basic circuit blocks:

- 1. Drivers
- 2. Receivers
- 3. The Exar proprietary charge pump

Drivers

The drivers are inverting level transmitters that convert TTL or CMOS logic levels to \pm 5.0V EIA/TIA-232 levels with an inverted sense relative to the input logic levels. Typically, the RS-232 output voltage swing is \pm 5.4V with no load and \pm 5V minimum fully loaded. The driver outputs are protected against infinite short-circuits to ground without degradation in reliability. Driver outputs will meet EIA/TIA-562 levels of +/-3.7V with supply voltages as low as 2.7V.

The drivers have a minimum data rate of 460kbps fully loaded with $3k\Omega$ in parallel with 1000pF, ensuring compatibility with PC-to-PC communication software.

Figure 6 shows a loopback test circuit used to test the RS-232 Drivers. Figure 7 shows the test results of the loopback circuit with all drivers active at 120kbps with RS-232 loads in parallel with a 1000pF capacitor. Figure 8 shows the test results where one driver was active at 460kbps and all drivers loaded with an RS-232 receiver in parallel with 1000pF capacitor. Designers should connect unused inputs to Vcc or GND.

Receivers

The Receivers convert EIA/TIA-232 levels to TTL or CMOS logic output levels. Since receiver input is usually from a transmission line where long cable lengths and system interference can degrade the signal, the inputs have a typical hysteresis margin of 300mV. This ensures that the receiver is virtually immune to noisy transmission lines. Should an input be left unconnected, an internal $5K\Omega$ pulldown resistor to ground will commit the output of the receiver to a HIGH state.

Charge Pump

The charge pump is an Exar-patended design (U.S. 5,306,954) and uses a unique approach compared to older less-efficient designs. The charge pump still requires four external capacitors, but uses a four-phase voltage shifting technique to attain symmetrical 5.5V power supplies. The internal power supply consists of a regulated dual charge pump that provides output voltages of +/-5.5V regardless of the input voltage (Vcc) over the +3.0V to +5.5V range.

In most circumstances, decoupling the power supply can be achieved adequately using a 0.1μ F bypass capacitor at C5 (refer to figure 5)

In applications that are sensitive to powersupply noise, decouple Vcc to ground with a capacitor of the same value as charge-pump capacitor C1. Physically connect bypass capacitors as close to the IC as possible.

The charge pump operates in a discontinuous mode using an internal oscillator. If the output voltages are less than a magnitude





Figure 6. SP3232EH Driver Loopback Test Circuit



Figure 7. Loopback Test results at 120kbps



of 5.5V, the charge pump is enabled. If the output voltages exceed a magnitude of 5.5V, the charge pump is disabled. This oscillator controls the four phases of the voltage shifting. A description of each phase follows.

Phase 1

- V_{ss} charge storage - During this phase of the clock cycle, the positive side of capacitors C_1 and C_2 are initially charged to V_{cc} . C⁺ is then switched to GND and the charge in C_1^- is transferred to C_2^- . Since C_2^+ is connected to V_{cc}, the voltage potential across capacitor C_2 is now 2 times V_{cc} .

Phase 2

— V_{ss} transfer — Phase two of the clock connects the negative terminal of C_2 to the V_{ss} storage capacitor and the positive terminal of C₂ to GND. This transfers a negative generated voltage to C_3 . This generated voltage is regulated to a minimum voltage of -5.5V. Simultaneous with the transfer of the voltage to C₃, the positive side of capacitor C₁ is switched to V_{cc} and the negative side is connected to GND.

Phase 3

 $-V_{DD}$ charge storage - The third phase of the clock is identical to the first phase — the charge transferred in C_1 produces $-V_{cc}$ in the negative terminal of C, which is applied to the negative side of capacitor C₂. Since C_2^+ is at V_{cc} , the voltage potential across $C_2^$ is 2 times V_{cc}.

Phase 4

 $- V_{DD}$ transfer — The fourth phase of the clock connects the negative terminal of C₂ to GND, and transfers this positive generated voltage across C_2 to C_4 , the V_{DD} storage capacitor. This voltage is regulated to +5.5V. At this voltage, the internal oscillator is disabled. Simultaneous with the transfer of the voltage to C_4 , the positive side of capacitor C₁ is switched to V_{cc} and the negative side is connected to GND, allowing the charge pump cycle to begin again. The charge pump cycle will continue as long as the operational conditions for the internal oscillator are present.

Since both V⁺ and V⁻ are separately generated from V_{cc}, in a no–load condition V⁺ and V⁻ will be symmetrical. Older charge pump approaches that generate V⁻ from V⁺ will show a decrease in the magnitude of V⁻ compared to V⁺ due to the inherent inefficiencies in the design.

The clock rate for the charge pump typically operates at greater than 250kHz. The external capacitors can be as low as 0.1μ F with a 16V breakdown voltage rating.



Figure 9. Charge Pump — Phase 1



Figure 10. Charge Pump — Phase 2



Figure 11. Charge Pump Waveforms

DESCRIPTION

SP3232EH_100_010611



Figure 12. Charge Pump — Phase 3



Figure 13. Charge Pump — Phase 4

ESD TOLERANCE

The **SP3232EH** device incorporates ruggedized ESD cells on all driver output and receiver input pins. The ESD structure is improved over our previous family for more rugged applications and environments sensitive to electro-static discharges and associated transients. The improved ESD tolerance is at least ±15kV without damage nor latch-up.

There are different methods of ESD testing applied:

a) MIL-STD-883, Method 3015.7 b) IEC61000-4-2 Air-Discharge c) IEC61000-4-2 Direct Contact

The Human Body Model has been the generally accepted ESD testing method for semi-conductors. This method is also specified in MIL-STD-883, Method 3015.7 for ESD testing. The premise of this ESD test is to simulate the human body's potential to store electro-static energy and discharge it to an integrated circuit. The simulation is performed by using a test model as shown in Figure 14. This method will test the IC's capability to withstand an ESD transient during normal handling such as in manufacturing areas where the IC's tend to be handled frequently.

The IEC-61000-4-2, formerly IEC801-2, is generally used for testing ESD on equipment and systems. For system manufacturers, they must guarantee a certain amount of ESD protection since the system itself is exposed to the outside environment and human presence. The premise with IEC61000-4-2 is that the system is required to withstand an amount of static electricity when ESD is applied to points and surfaces of the equipment that are accessible to personnel during normal usage. The transceiver IC receives most of the ESD current when the ESD source is applied to the connector pins. The test circuit for IEC61000-4-2 is shown on Figure 15. There are two methods within IEC61000-4-2, the Air Discharge method and the Contact Discharge method.

With the Air Discharge Method, an ESD voltage is applied to the equipment under test (EUT) through air. This simulates an electrically charged person ready to connect a cable onto the rear of the system only to find an unpleasant zap just before the person touches the back panel. The high energy potential on the person discharges through an arcing path to the rear panel of the system before he or she even touches the system. This energy, whether discharged directly or through air, is predominantly a function of the discharge current rather than the discharge voltage. Variables with an air discharge such as approach speed of the object carrying the ESD potential to the system and humidity will tend to change the discharge current. For example, the rise time of the discharge current varies with the approach speed.

The Contact Discharge Method applies the ESD current directly to the EUT. This method was devised to reduce the unpredictability of the ESD arc. The discharge current rise time is constant since the energy is directly transferred without the air-gap arc. In situations such as hand held systems, the ESD charge can be directly discharged to the





Figure 15. ESD Test Circuit for IEC61000-4-2

equipment from a person already holding the equipment. The current is transferred on to the keypad or the serial port of the equipment directly and then travels through the PCB and finally to the IC.

The circuit models in Figures 14 and 15 represent the typical ESD testing circuit used for all three methods. The C_s is initially charged with the DC power supply when the first switch (SW1) is on. Now that the capacitor is charged, the second switch (SW2) is on while SW1 switches off. The voltage stored in the capacitor is then applied through R_s , the current limiting resistor, onto the device under test (DUT). In ESD tests, the SW2 switch is pulsed so that the device under test receives a duration of voltage.

For the Human Body Model, the current limiting resistor (R_s) and the source capacitor (C_s) are 1.5k Ω an 100pF, respectively. For IEC-61000-4-2, the current limiting resistor (R_s) and the source capacitor (C_s) are 330 Ω an 150pF, respectively.

The higher C_s value and lower R_s value in the IEC61000-4-2 model are more stringent than the Human Body Model. The larger storage capacitor injects a higher voltage to the test point when SW2 is switched on. The lower current limiting resistor increases the current charge onto the test point.



Figure 16. ESD Test Waveform for IEC61000-4-2

DEVICE PIN TESTED	HUMAN BODY MODEL	Air Discharge	IEC61000-4-2 Direct Contact	Level
Driver Outputs	<u>+</u> 15kV	<u>+</u> 15kV	<u>+</u> 8kV	4
Receiver Inputs	<u>+</u> 15kV	<u>+</u> 15kV	<u>+</u> 8kV	4

Table 2. Transceiver ESD Tolerance Levels

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PACKAGE: 16 PIN SSOP



PACKAGE: 16 PIN PDIP



PACKAGE: 16 PIN SOICW



PACKAGE: 16 PIN TSSOP



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ORDERING INFORMATION

Part Number	Temp. Range	Package
SP3232EHCA-L	0°C to +70°C	16 Pin SSOP
SP3232EHCA-L/TR	0°C to +70°C	16 Pin SSOP
SP3232EHCP-L	0°C to +70°C	16 Pin PDIP
SP3232EHCT-L	0°C to +70°C	16 Pin WSOIC
SP3232EHCT-L/TR	0°C to +70°C	16 Pin WSOIC
SP3232EHCY-L	0°C to +70°C	16 Pin TSSOP
SP3232EHCY-L/TR	0°C to +70°C	16 Pin TSSOP
SP3232EHEA-L	-40°C to +85°C	16 Pin SSOP
SP3232EHEA-L/TR	-40°C to +85°C	16 Pin SSOP
SP3232EHEP-L	-40°C to +85°C	16 Pin PDIP
SP3232EHET-L	-40°C to +85°C	16 Pin WSOIC
SP3232EHET-L/TR	-40°C to +85°C	16 Pin WSOIC
SP3232EHEY-L	-40°C to +85°C	16 Pin TSSOP
SP3232EHEY-L/TR	-40°C to +85°C	16 Pin TSSOP

Note: "/TR" is for tape and Reel option. "-L" is for lead free packaging

REVISION HISTORY

DATE	REVISION	DESCRIPTION
01/18/06		Legacy Sipex Datasheet
01/06/11	1.0.0	Convert to Exar Format, Remove EOL device SP3222EH, update ordering information and change revision to 1.0.0.

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